

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| L1 | 2100 | (laser near (annealing annealed)) near1 (process method substrate) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 15:48 |
| L2 | 1 | 1 with (gate near (region dielectric)) with (("source/drain" (source near drain))) near1 region) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 15:38 |
| L3 | 7540 | (laser near (annealing annealed)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 15:48 |
| L4 | 10 | 3 with (gate near (region dielectric)) with (("source/drain" (source near drain))) near1 region) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 15:40 |
| L5 | 11 | 3 with (gate near (region dielectric)) with ("source/drain" (source near drain)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 15:39 |
| L6 | 16 | 3 with (gate near (insulative insulation region dielectric)) with (("source/drain" (source near drain))) near1 region) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 15:48 |
| L7 | 8013 | (laser near (anneal annealing annealed)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:51 |
| L8 | 18 | 7 with (gate near (insulative insulation region dielectric)) with (("source/drain" (source near drain))) near1 region) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 16:29 |
| L9 | 32 | "5518940" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 16:27 |

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| L10 | 45 | "5523257" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 16:28 |
| L11 | 37 | "5563427" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 16:28 |
| L12 | 50 | "5620905" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 16:28 |
| L13 | 21 | "6307214" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 16:28 |
| L14 | 18 | "5474940" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 16:28 |
| L15 | 189 | 9 10 11 12 13 14 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 16:28 |
| L16 | 133 | 15 and laser | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 16:28 |
| L17 | 124 | 16 and (anneal annealing annealed) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 18:36 |
| L18 | 65 | 17 and (gate near (metal electrode insulative insulation region dielectric)) with (("source/drain" (source near drain)) near1 region) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:18 |
| L19 | 59 | 18 and metal | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:09 |

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| L20 | 2 | 8 and 19 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:09 |
| L21 | 75 | 8 19 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:27 |
| L22 | 0 | 21 and (electron near volt) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:10 |
| L23 | 504 | (work near function) with (electron near volt) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:10 |
| L24 | 190 | 23 with metal | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:11 |
| L25 | 29 | 24 and gate | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:11 |
| L26 | 6 | 17 and (metal near gate) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:19 |
| L27 | 26 | 21 and (implanted implanting) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:48 |
| L28 | 1 | 21 and (laser near4 (implanted implanting)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:49 |
| L29 | 6 | 21 and (laser with (implanted implanting)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:49 |

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| L30 | 8919 | (laser near2 (anneal annealing annealed)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:51 |
| L31 | 74 | 30 and ((gate near1 (oxide insulative insulation dielectric)) near3 metal) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:53 |
| L32 | 36 | 30 and ((gate near1 (oxide insulative insulation dielectric)) near3 (metal near layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:54 |
| L33 | 36 | 30 and ((gate near1 (oxide insulative insulation dielectric)) near3 (metal near1 layer)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 17:54 |
| L34 | 17 | 25 and (anneal annealing annealed) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/05/30 18:36 |